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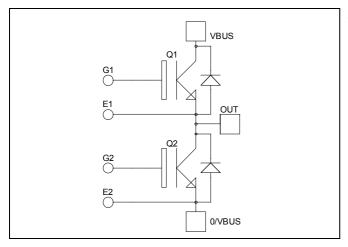


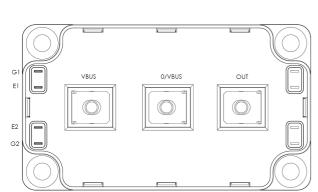




Phase leg Fast Trench + Field Stop IGBT3 Power Module







Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Fast Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_{C}	Continuous Collector Current	$T_C = 25^{\circ}C$	420	
1C	Continuous Conector Current	$T_C = 80$ °C	300	A
I_{CM}	Pulsed Collector Current	$T_C = 25$ °C	600	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	1380	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	600A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				500	μΑ
V _{CE(sat)}	Collector Emitter Saturation Voltage	V GE 13 V	$T_j = 25$ °C	1.4	1.7	2.1	V
			$T_j = 125$ °C		2.0		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 4 \text{ mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA

Dynamic Characteristics

·	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		21		nF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		1.2		
C_{res}	Reverse Transfer Capacitance	f = 1MHz		0.9		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		260		ns
T_{r}	Rise Time	$V_{GE} = \pm 15V$		30		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 300A$		420		
T_{f}	Fall Time	$R_G = 1.8\Omega$		70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		290		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$		50		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ - $I_C = 300A$		520		
T_{f}	Fall Time	$R_G = 1.8\Omega$		90		
Eon	Turn on Energy	$V_{GE} = \pm 15V \ V_{Bus} = 600V$ $T_j = 125^{\circ}C$		30		m I
E_{off}	Turn off Energy	$I_C = 300A$ $R_G = 1.8\Omega$ $T_j = 125^{\circ}C$		30		mJ

Reverse diode ratings and characteristics

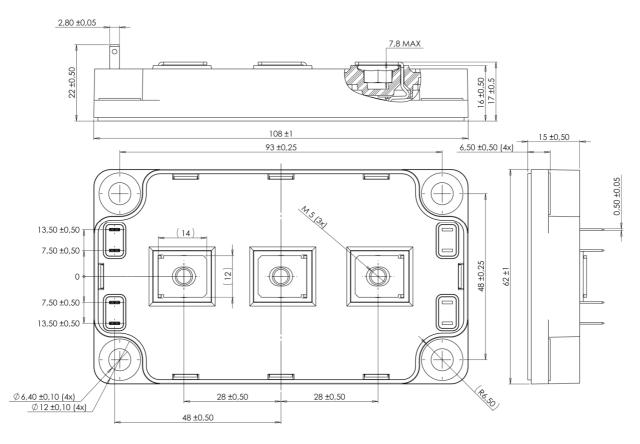
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_i = 25$ °C $T_i = 125$ °C			500 700	μА
I_{F}	DC Forward Current		$T_{c} = 80^{\circ}C$		300	700	A
V	V_F Diode Forward Voltage $I_F = 300A$ $V_{GE} = 0V$	$I_F = 300A$	$T_i = 25^{\circ}C$		1.6	2.1	V
v _F		$V_{GE} = 0V$	$T_{i} = 125^{\circ}C$		1.6		·
t_{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		170		ns
·rr	Reverse Recovery Time		$T_j = 125$ °C		280		113
0	Reverse Recovery Charge	$I_F = 300A$ $V_R = 600V$	$T_j = 25^{\circ}C$		27		μС
Q_{rr}	Reverse Recovery Charge	$di/dt = 3000A/\mu s$	$T_{i} = 125^{\circ}C$		54		μС
Б	Davanga Dagayany Emanay		$T_j = 25$ °C		15		mJ
E_{r}	Reverse Recovery Energy		$T_j = 125$ °C		27		1113



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit		
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.09	°C/W		
			Diode			0.17			
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V		
T_{J}	Operating junction temperature range			-40		150	50		
T_{STG}	Storage Temperature Range	Temperature Range -40 125				125	°C		
$T_{\rm C}$	Operating Case Temperature			-40		100			
Torque	Mounting torque	To heatsink	M6	3		5	N.m		
		For terminals	M5	2		3.5	18.111		
Wt	Package Weight					300	g		

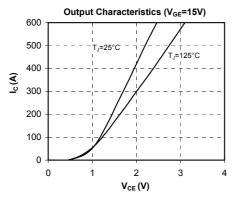
SP6 Package outline (dimensions in mm)

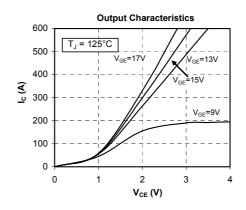


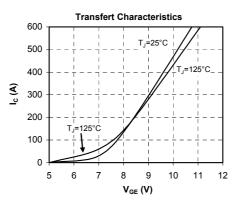
 $See \ application \ note \ APT0601 - Mounting \ Instructions \ for \ SP6 \ Power \ Modules \ on \ www.microsemi.com$

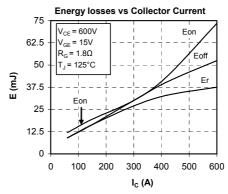


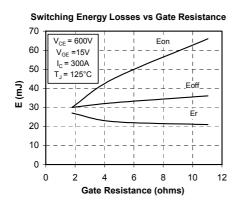
Typical Performance Curve

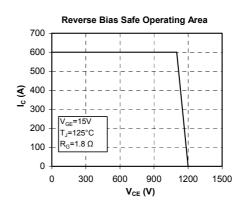


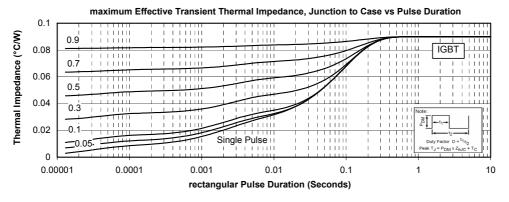




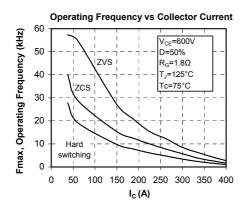


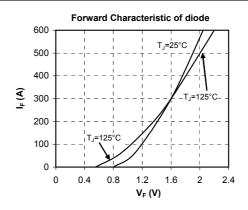


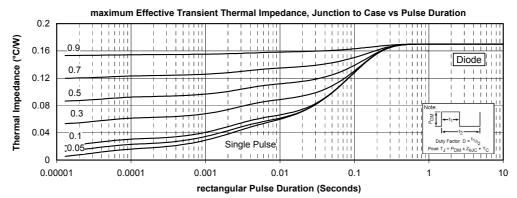














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